

AN 1989-155239 [21] WPIIDS
DNN N1989-118216 DNC C1989-068848
TI Clad target sputtering material - includes copper substrate containing zinc, indium, manganese, antimony beryllium, calcium, etc..
DC M13 U11
PA (TANI) TANAKA KIKINZOKU KOGYO KK
CYC 1
PI JP 01096374 A 19890414 (198921)* 3<--
ADT JP 01096374 A JP 1987-251174 19871005
PRAI JP 1987-251174 19871005
AB JP 01096374 A UPAB: 19930923

A sputtering clad target material is composed of target material clad through metal bonding agent to a more than 99.7% purity Cu substrate including at least one of Zn, In, Mn, Sb, Be, Ca, Cr, Te, Y, Nb, Mo, Ta and Sn 100-3000 weight ppm in total. The substrate contacting a backing plate is not pressure-bonded.

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